

Automotive N-channel 60 V, 1.6 mΩ typ., 180 A STripFET™ F6
Power MOSFET in H²PAK-2 and H²PAK-6 packages

Datasheet - production data

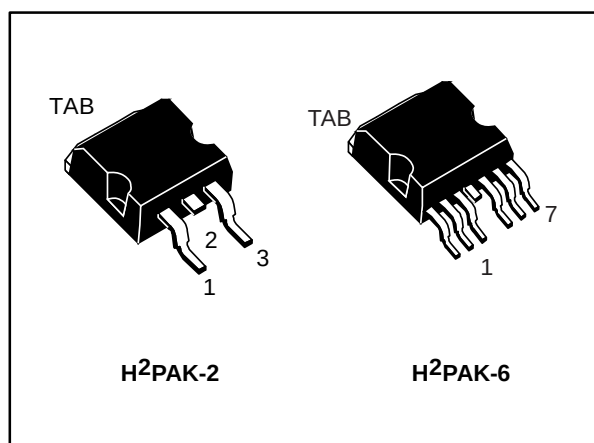
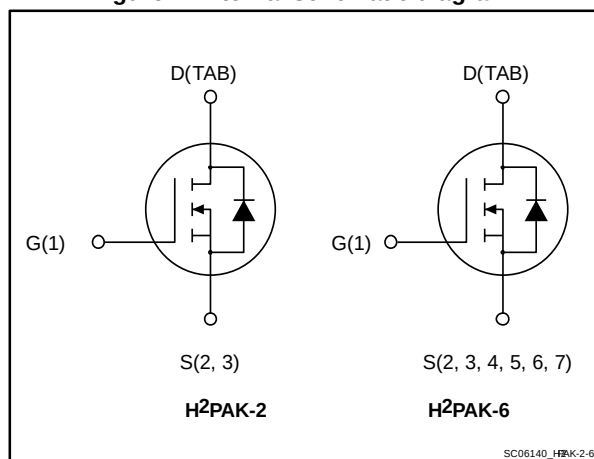


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max	I _D
STH265N6F6-2AG	60 V	2.1 mΩ	180 A
STH265N6F6-6AG	60 V	2.1 mΩ	180 A

- Designed for automotive applications
- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the STripFET™ F6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R_{DS(on)} in all packages.

Table 1: Device summary

Order code	Marking	Package	Packaging
STH265N6F6-2AG	265N6F6	H ² PAK-2	Tape and reel
STH265N6F6-6AG	265N6F6	H ² PAK-6	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	60	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	180	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	180	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	300	W
E_{AS}	Single pulse avalanche energy (Starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = 80\text{ A}$)	720	mJ
	Derating factor	2	W/ $^{\circ}\text{C}$
T_{stg}	Storage temperature	- 55 to 175	$^{\circ}\text{C}$
T_J	Operating junction temperature		

Notes:

⁽¹⁾Current limited by package.

⁽²⁾ Pulse width limited by safe operating area.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	$^{\circ}\text{C/W}$

Notes:

⁽¹⁾When mounted on FR-4 board of 1 inch², 2 oz Cu.

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage (V _{GS} = 0)	I _D = 250 μA	60			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = 60 V			1	μA
		V _{DS} = 60 V, T _C = 125 °C			100	μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2		4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 60 A		1.6	2.1	mΩ

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0	-	11800	-	pF
C _{oss}	Output capacitance		-	1235	-	pF
C _{rss}	Reverse transfer capacitance		-	488	-	pF
Q _g	Total gate charge	V _{DD} = 30 V, I _D = 120 A, V _{GS} = 10 V	-	183	-	nC
Q _{gs}	Gate-source charge		-	53	-	nC
Q _{gd}	Gate-drain charge		-	41	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 30 V, I _D = 60 A R _G = 4.7 Ω, V _{GS} = 10 V	-	31	-	ns
t _r	Rise time		-	165	-	ns
t _{d(off)}	Turn-off-delay time		-	144	-	ns
t _f	Fall time		-	63	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				180	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				720	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 180 \text{ A}$, $V_{GS} = 0$			1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 120 \text{ A}$, $V_{DD} = 48 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$, $T_j = 150 \text{ }^\circ\text{C}$	-	56	-	ns
Q_{rr}	Reverse recovery charge		-	116	-	nC
I_{RRM}	Reverse recovery current		-	3.8	-	A

Notes:

⁽¹⁾ Pulse width limited by safe operating area.

⁽²⁾ Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.2 Electrical characteristics (curves)

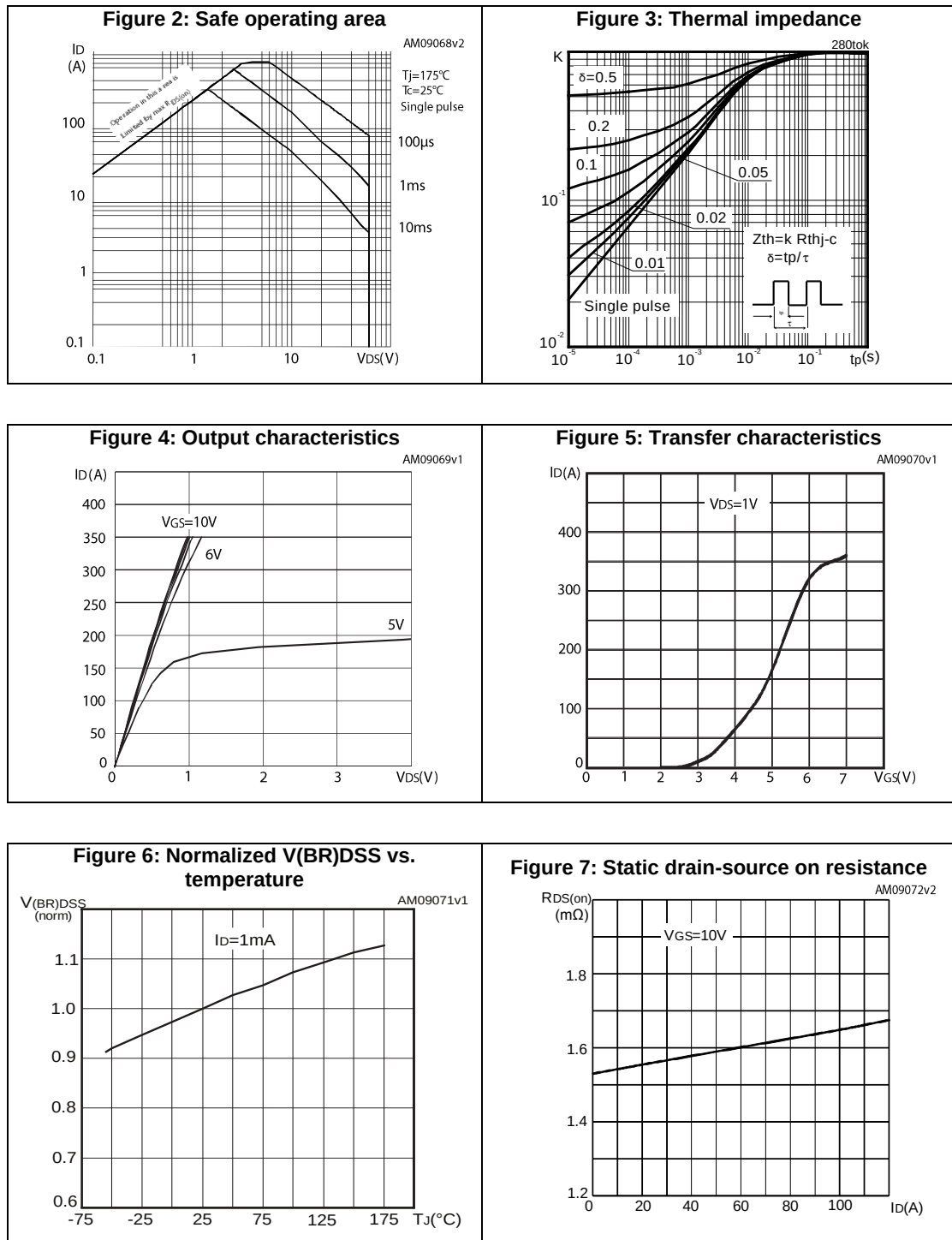


Figure 8: Gate charge vs. gate-source voltage

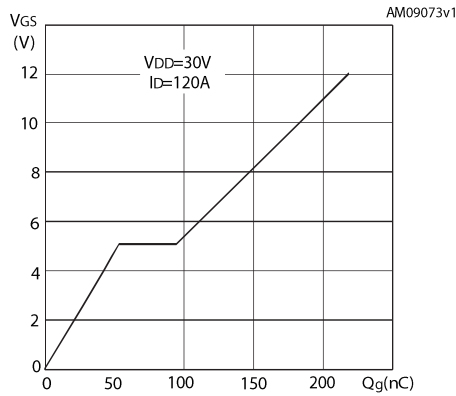


Figure 9: Capacitance variations

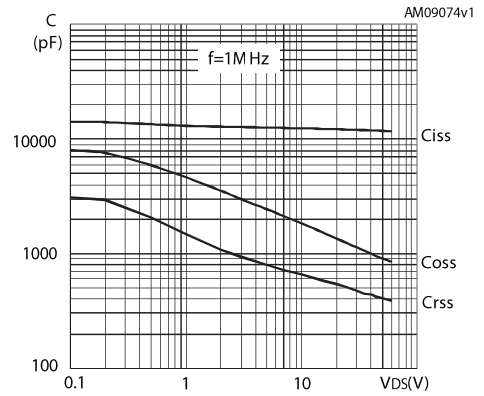


Figure 10: Normalized gate threshold voltage vs. temperature

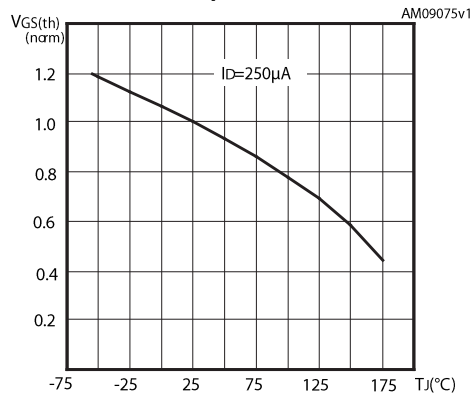


Figure 11: Normalized on resistance vs. temperature

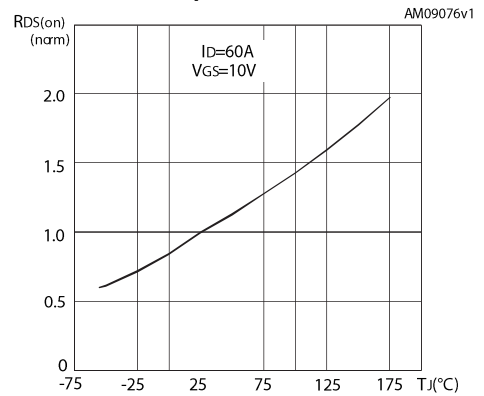
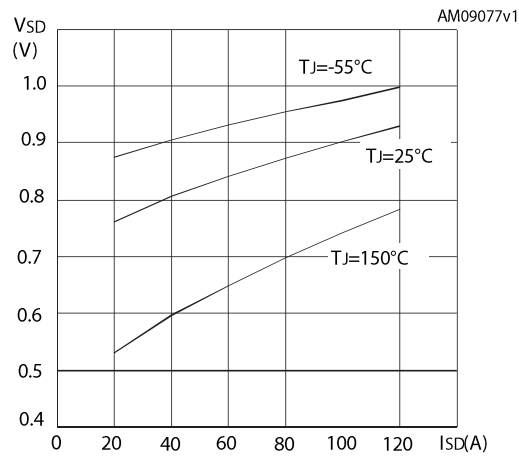


Figure 12: Source-drain diode forward characteristics



3 **Package mechanical data**

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3.1 H2PAK-2 mechanical data

Figure 13: H²PAK-2 outline

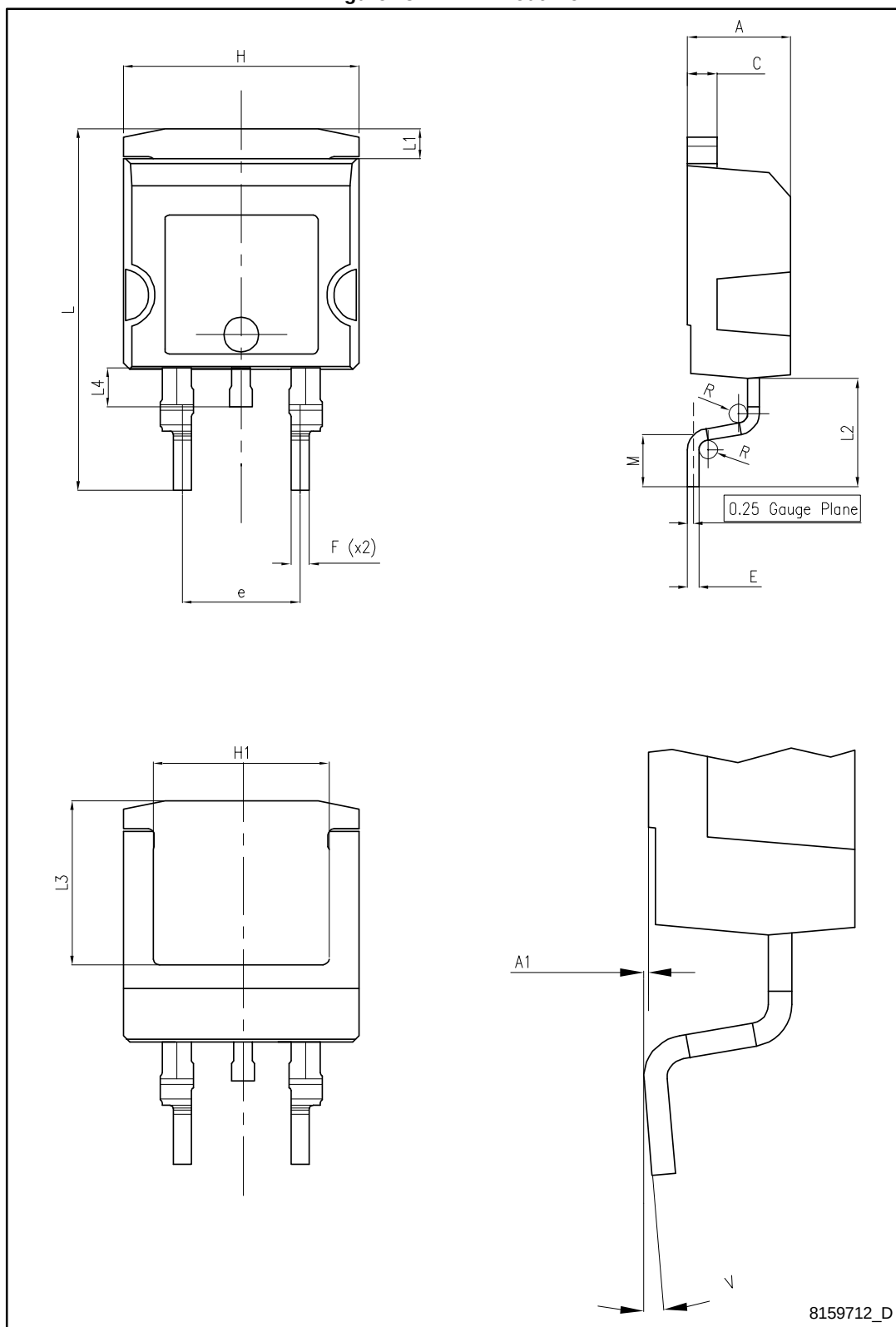
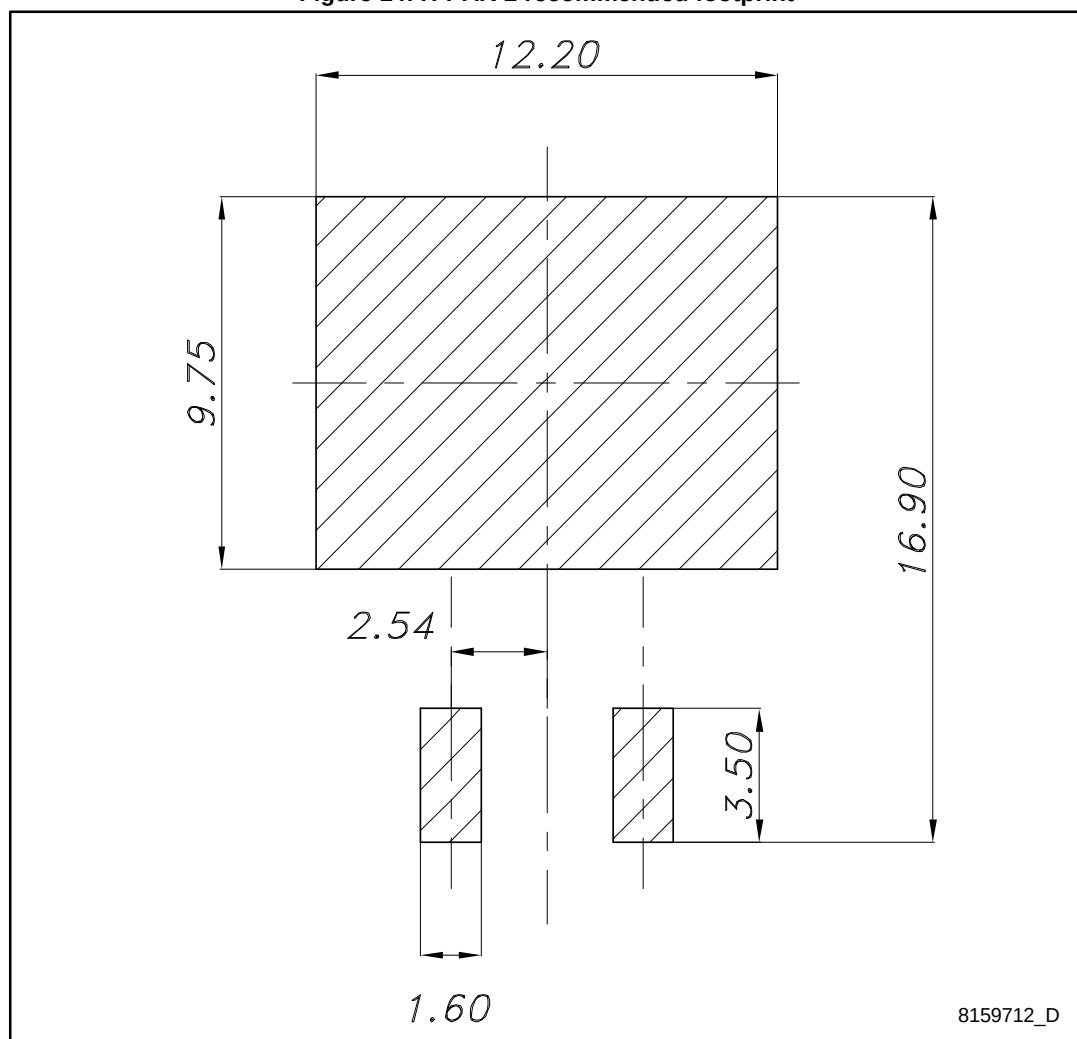


Table 8: H²PAK-2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 14: H²PAK-2 recommended footprint



3.2 H²PAK-6 package information

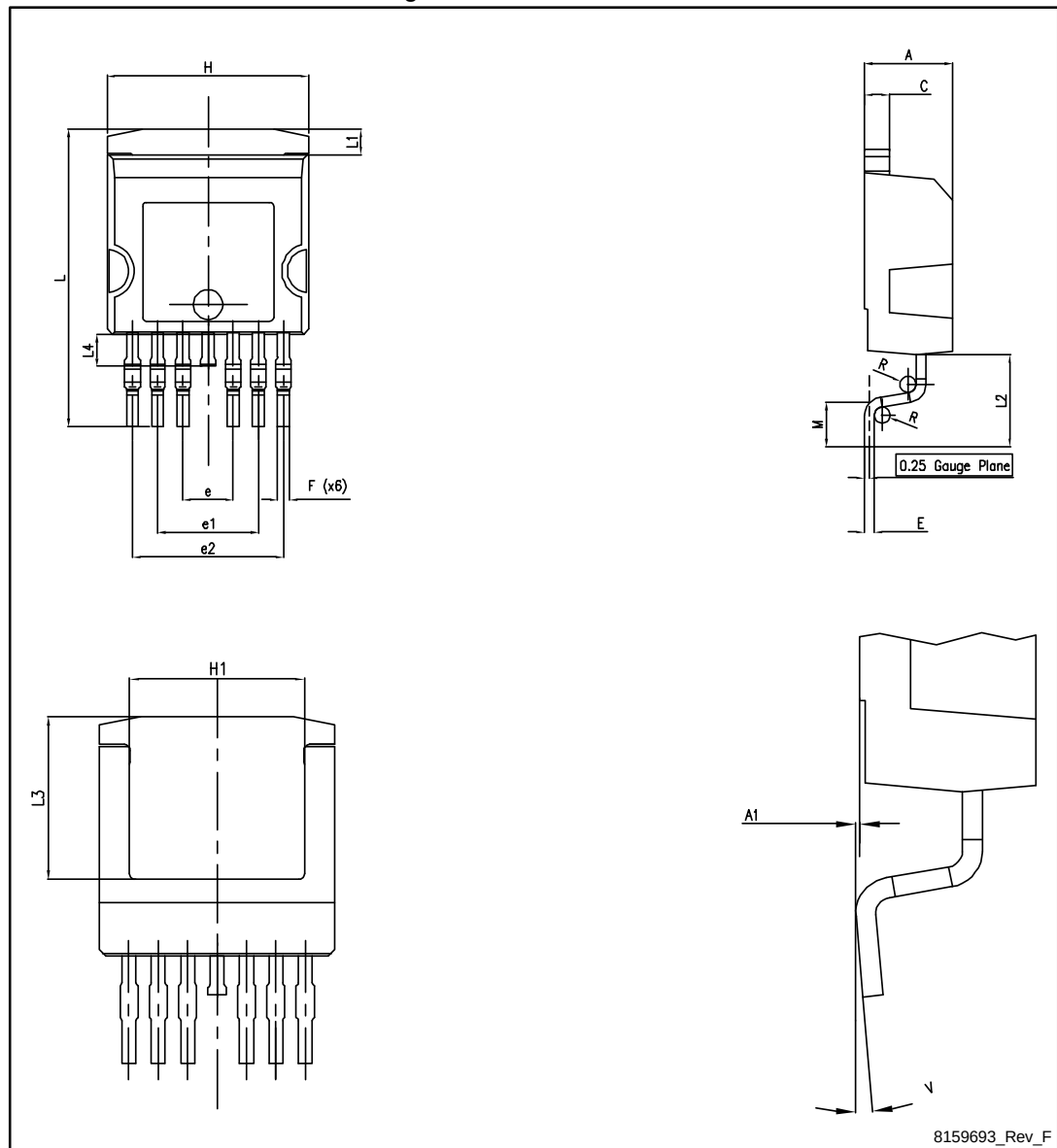
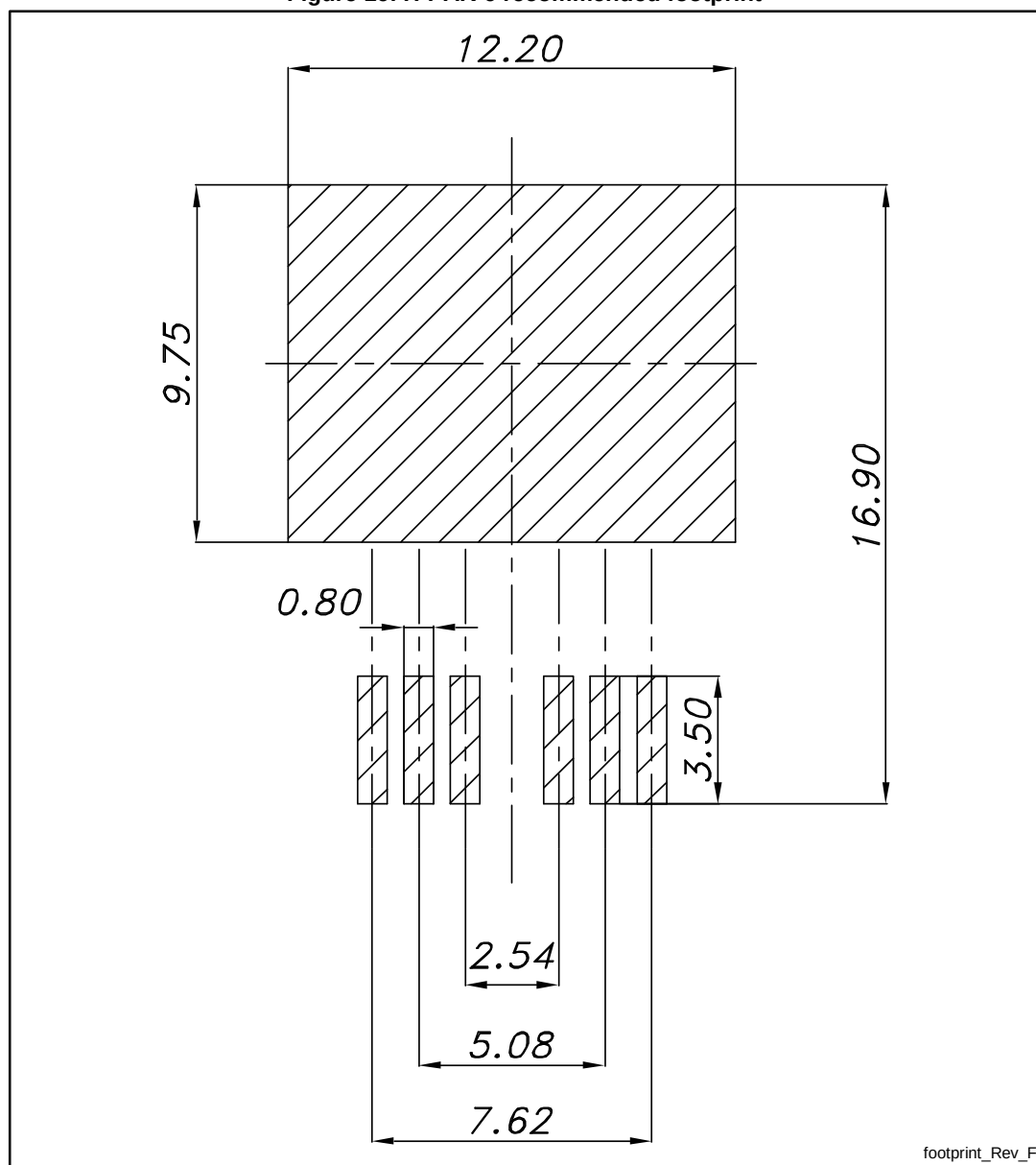
Figure 15: H²PAK-6 outline

Table 9: H²PAK-6 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	2.34		2.74
e1	4.88		5.28
e2	7.42		7.82
E	0.45		0.60
F	0.50		0.70
H	10.00		10.40
H1	7.40		7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.5		1.75
M	1.90		2.50
R	0.20		0.60
V	0°		8°

Figure 16: H²PAK-6 recommended footprint

Dimensions are in mm.

4 Packaging information

Figure 17: Tape outline

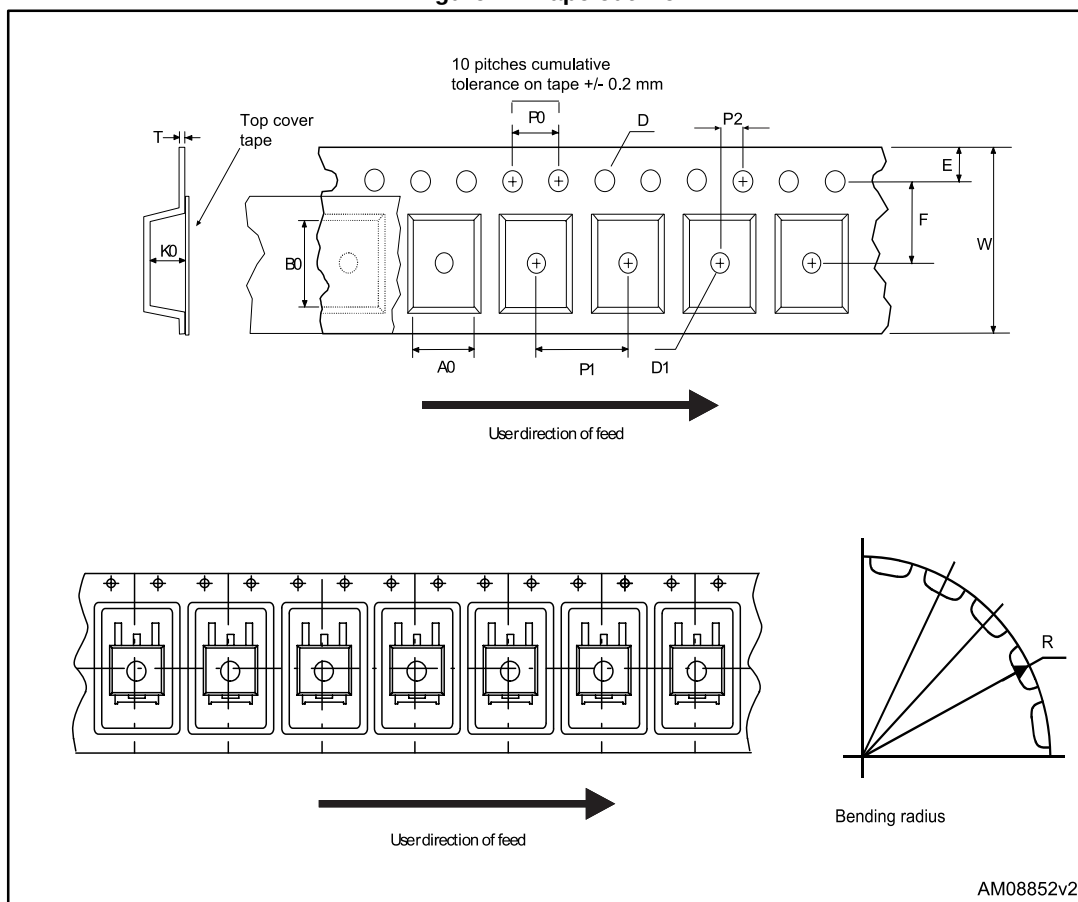


Figure 18: Reel outline

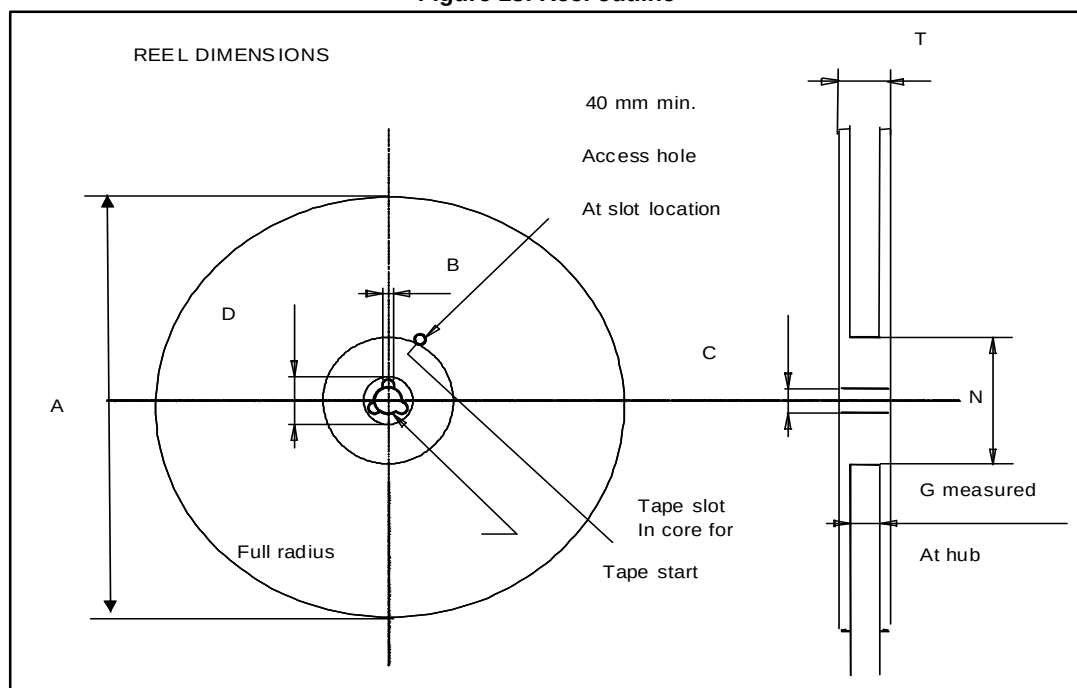


Table 10: Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

5 Revision history

Table 11: Document revision history

Date	Revision	Changes
13-Oct-2014	1	First release.
18-Dec-2014	2	Document status promoted from preliminary to production data.

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